

3. (Amended) A liquid crystal panel substrate comprising:

B²
a pixel region having a matrix of reflecting electrodes formed on a substrate and a switching element formed corresponding to each of said reflecting electrodes, a periphery region of said pixel region on the substrate having at least insulating interlayers; and

a passivation film having a laminate structure comprising a silicon oxide film and a silicon nitride film on said silicon oxide film, the passivation film being formed at least on a side of edge sections of the at least insulating interlayers.

4. (Amended) A liquid crystal panel substrate comprising:

a pixel region having a matrix of reflecting electrodes formed on a substrate and a transistor formed corresponding to each of the reflecting electrodes;

a peripheral circuit arranged in a periphery region of said pixel region on the substrate for supplying signals to said transistors in said pixel region;

a first passivation film comprising a silicon oxide film formed on said reflecting electrodes in said pixel region; and

a second passivation film comprising a silicon nitride film formed at least on a side of edge sections of said periphery region.

- B³
9. (Amended) A liquid crystal panel substrate according to claim 3, said edge section of said insulating interlayers being a scribed region of the substrate.

Please add new claims 14 and 15 as follows: /

- B⁴
--14. A liquid crystal panel substrate, comprising:

reflecting electrodes formed on a substrate;

a switching element formed corresponding to each of the reflecting electrodes;

a passivation film formed on the reflecting electrodes comprising a silicon oxide film; and

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a silicon nitride film formed as an insulating interlayer between the reflecting electrodes and the switching element so as to cover the switching element except for a connection portion between the reflecting electrode and the switching element.--

--15. The liquid crystal substrate according to claim 7, the second silicon oxide layer being the same layer as the first silicon oxide layer.--

REMARKS

Claims 1-15 are pending. By this Amendment, claims 1, 3, 4 and 9 are amended and claims 14 and 15 are added. Reconsideration based on the following remarks is respectfully requested.

The attached Appendix includes marked-up copies of each rewritten claim (37 C.F.R. §1.121(c)(1)(ii)).

Applicant gratefully acknowledges that the Office Action indicates that claims 7, 12 and 13 are allowable.

I. THE CLAIMS DEFINE PATENTABLE SUBJECT MATTER

The Office Action rejects claim 1 under 35 U.S.C. §103(a) as unpatentable over U.S. Patent No. 5,767,827 to Kobayashi et al. ("Kobayashi") in view of U.S. Patent No. 5,805,252 to Shimada et al. ("Shimada"); claim 2 under 35 U.S.C. §103(a) as unpatentable over Kobayashi and Shimada in view of U.S. Patent No. 5,056,895 to Kahn ("Kahn"); claims 3, 8 and 9 under 35 U.S.C. §103(a) as unpatentable over U.S. Patent No. 5,510,918 to Matsunaga et al. ("Matsunaga") in view of Kahn; claim 4 under 35 U.S.C. §103(a) as unpatentable over Kobayashi in view of Matsunaga; claim 5 under 35 U.S.C. §103(a) as unpatentable over Kobayashi in view of Shimada; claim 6 under 35 U.S.C. §103(a) as unpatentable over Kobayashi in view of Kahn; and claims 10 and 11 under 35 U.S.C. §103(a) as unpatentable over Matsunaga in view of Kahn. These rejections are respectfully traversed.